40 Watt Peak Power Zener Surge Protection Device

SC−70 Dual Common Cathode Zeners

MMBZ27VCW

These dual monolithic silicon zener diodes are designed for applications requiring transient overvoltage protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common cathode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

Specification Features:

- SC−70 Package Allows Either Two Separate Unidirectional Configurations or a Single Bidirectional Configuration
- Working Peak Reverse Voltage Range − 22 V
- Standard Zener Breakdown Voltage − 27 V
- Peak Power − 40 W @ 1.0 ms (Bidirectional), per Figure 4 Waveform
- ESD Rating of Class N (exceeding 16 kV) per the Human Body Model
- Low Leakage < 100 nA
- Flammability Rating: UL 94 V−O
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Mechanical Characteristics:

CASE: Void-free, transfer-molded, thermosetting plastic case

FINISH: Corrosion resistant finish, easily solderable

MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES: 260°C for 10 Seconds

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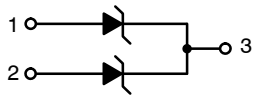
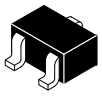
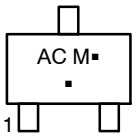


PIN 1. ANODE
2. ANODE
3. CATHODE



SC−70
CASE 419
STYLE 4

MARKING DIAGRAM



AC = Specific Device Code
M = Date Code
▪ = Pb−Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
MMBZ27VCWT1G	SC−70 (Pb−Free)	3000 / Tape & Reel
SZMMBZ27VCWT1G	SC−70 (Pb−Free)	3000 / Tape & Reel
MMBZ27VCWT3G	SC−70 (Pb−Free)	10000 / Tape & Reel
SZMMBZ27VCWT3G	SC−70 (Pb−Free)	10000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MAXIMUM RATINGS

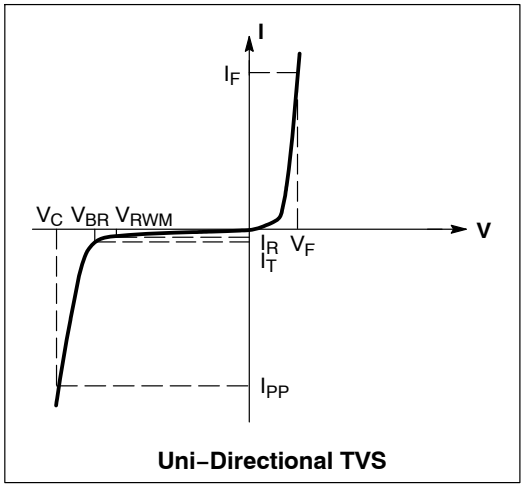
Rating	Symbol	Value	Unit
Peak Power Dissipation @ 1.0 ms (Note 1) @ $T_L \le 25°C$	P_{pk}	40	Watts
Total Power Dissipation on FR−5 Board (Note 2) @ $T_A = 25°C$ Derate above 25°C	P_D	200 1.6	mW mW/°C
Thermal Resistance Junction−to−Ambient	$R_{\theta JA}$	618	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	− 55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. Nonrepetitive current pulse per Figure 4 and derate above $T_A = 25°C$ per Figure 5.
2. FR−5 = 1.0 x 0.75 x 0.62 in.

ELECTRICAL CHARACTERISTICS
($T_A = 25°C$ unless otherwise noted)

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or 2 and 3)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
V_{BR}	Maximum Temperature Coefficient of V_{BR}
I_F	Forward Current
V_F	Forward Voltage @ I_F



Uni−Directional TVS

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted)

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or Pins 2 and 3)

(V_F = 1.1 V Max @ I_F = 200 mA)

Device	Device Marking	V_{RWM}	I_R @ V_{RWM}	Breakdown Voltage				V_C @ I_{PP} (Note 4)		V_{BR}
				V_{BR} (Note 3) (V)			@ I_T	V_C	I_{PP}	
		Volts	nA	Min	Nom	Max	mA	V	A	mV/°C
MMBZ27VCWT1G, SZMMBZ27VCWT1G, MMBZ27VCWT3G, SZMMBZ27VCWT3G	AC	22	50	25.65	27	28.35	1.0	38	1.0	26

3. V_{BR} measured at pulse test current I_T at an ambient temperature of 25°C.
4. Surge current waveform per Figure 4 and derate per Figure 5

TYPICAL CHARACTERISTICS

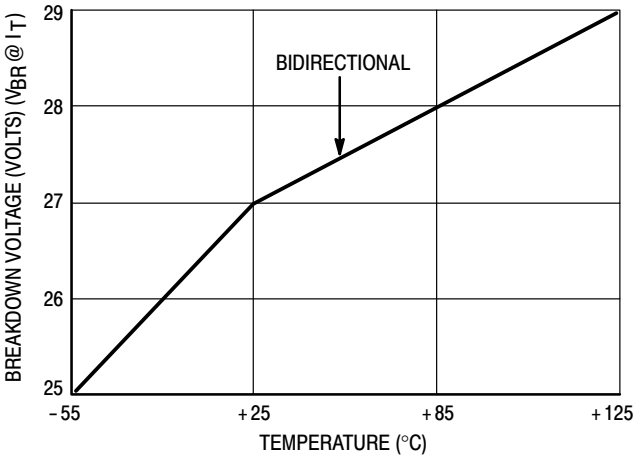


Figure 1. Typical Breakdown Voltage versus Temperature

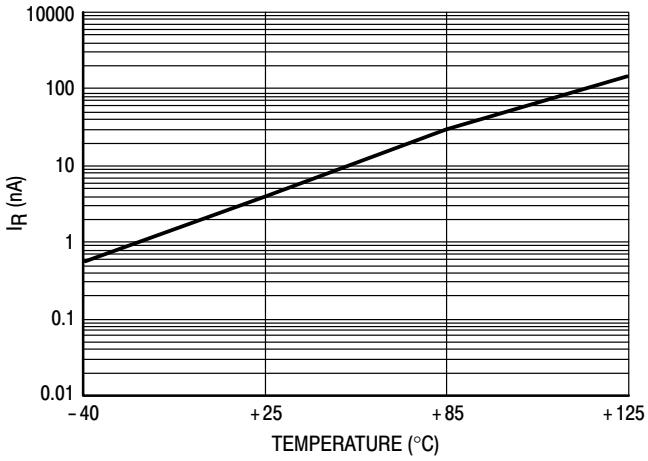


Figure 2. Typical Leakage Current versus Temperature

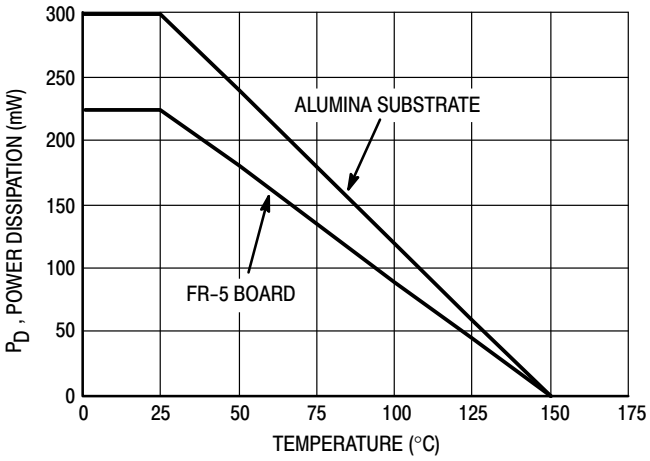


Figure 3. Steady State Power Derating Curve

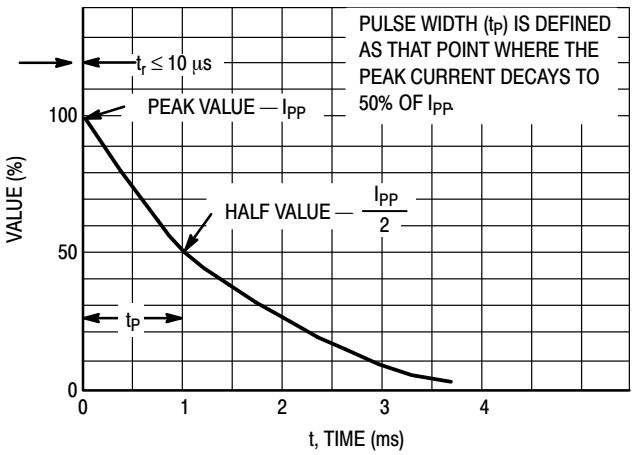


Figure 4. Pulse Waveform

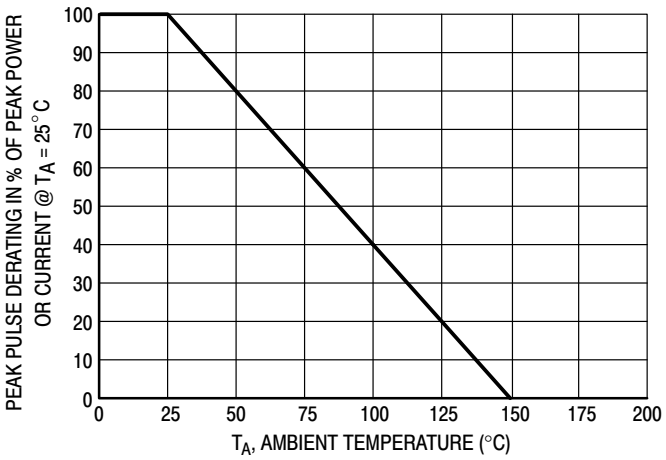
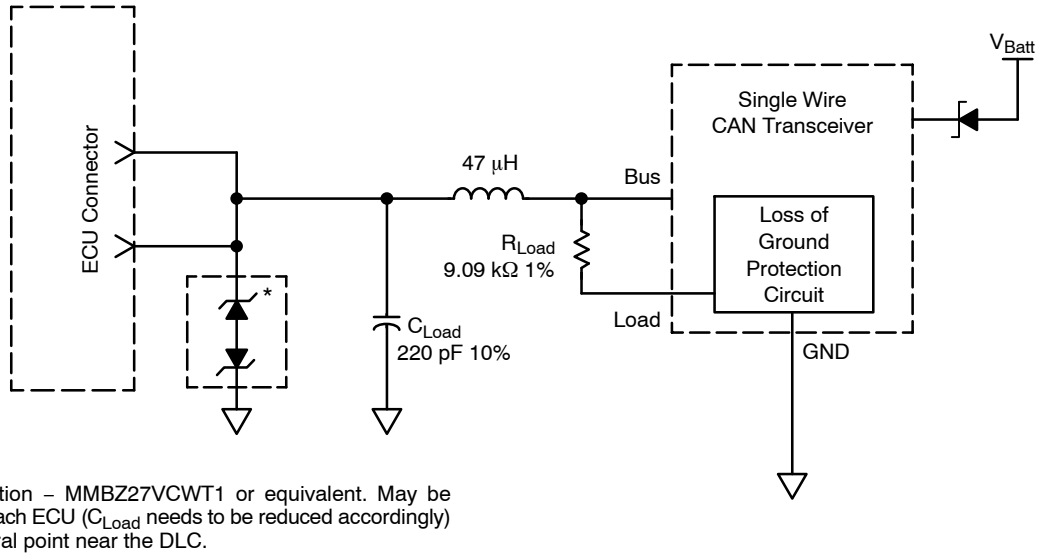


Figure 5. Pulse Derating Curve

TYPICAL APPLICATIONS

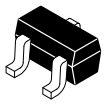


*ESD Protection – MMBZ27VCWT1 or equivalent. May be located in each ECU (C_{Load} needs to be reduced accordingly) or at a central point near the DLC.

Figure 6. Single Wire CAN Network

Figure is the recommended solution for transient EMI/ESD protection. This circuit is shown in the Society of Automotive Engineers February, 2000 J2411 “Single Wire CAN Network for Vehicle Applications” specification (Figure 6, page 11). Note: the dual common anode zener configuration shown above is electrically equivalent to a dual common cathode zener configuration.

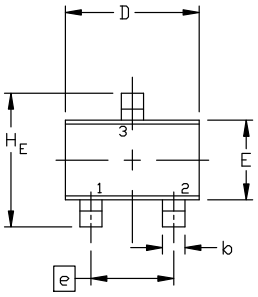
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



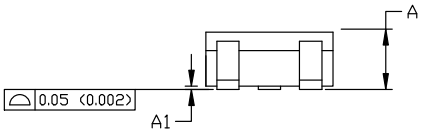
SCALE 4:1

SC−70 (SOT−323)
CASE 419
ISSUE R

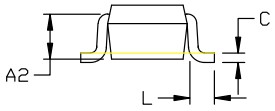
DATE 11 OCT 2022



TOP VIEW



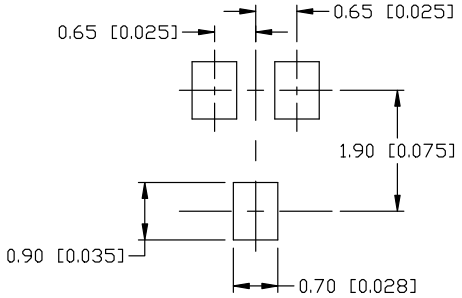
SIDE VIEW



END VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

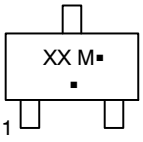
	MILLIMETERS			INCHES		
DIM	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H_E	2.00	2.10	2.40	0.079	0.083	0.095



* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOLDERING FOOTPRINT

GENERIC MARKING DIAGRAM



XX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
CANCELLED

STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE

STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 6:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 7:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 8:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 10:
PIN 1. CATHODE
2. ANODE
3. ANODE−CATHODE

STYLE 11:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

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